AMD Xilinx - XCZU5CG-2FBVB900I Datasheet

Welcome to E-XFL.COM

Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 256K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	900-BBGA, FCBGA
Supplier Device Package	900-FCBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu5cg-2fbvb900i

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[(1)]	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 5: **PS MIO Pull-up and Pull-down Current**

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 3.3V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 2.5V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 1.8V.	15	65	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 2.5V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	15	65	µA

Table 19: **Complementary Differential SelectIO DC Input and Output Levels for HP I/O Banks(1)**

I/O Standard	V_{ICM} (V)(2)			V_{ID} (V)(3)		V_{OL} (V)(4)	V_{OH} (V)(5)	I_{OL}	I_{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.680	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	0.400	$V_{CCO} - 0.400$	5.8	–5.8
DIFF_HSTL_I_12	0.400 x V_{CCO}	$V_{CCO}/2$	0.600 x V_{CCO}	0.100	–	0.250 x V_{CCO}	0.750 x V_{CCO}	4.1	–4.1
DIFF_HSTL_I_18	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	0.400	$V_{CCO} - 0.400$	6.2	–6.2
DIFF_HSUL_12	$(V_{CCO}/2) - 0.120$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.120$	0.100	–	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
DIFF_SSTL12	$(V_{CCO}/2) - 0.150$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	8.0	–8.0
DIFF_SSTL135	$(V_{CCO}/2) - 0.150$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	9.0	–9.0
DIFF_SSTL15	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	10.0	–10.0
DIFF_SSTL18_I	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	$(V_{CCO}/2) - 0.470$	$(V_{CCO}/2) + 0.470$	7.0	–7.0

Notes:

1. DIFF_POD10 and DIFF_POD12 HP I/O bank specifications are shown in Table 20, Table 21, and Table 22.
2. V_{ICM} is the input common mode voltage.
3. V_{ID} is the input differential voltage.
4. V_{OL} is the single-ended low-output voltage.
5. V_{OH} is the single-ended high-output voltage.

Table 20: **DC Input Levels for Differential POD10 and POD12 I/O Standards(1)(2)**

I/O Standard	V_{ICM} (V)			V_{ID} (V)	
	Min	Typ	Max	Min	Max
DIFF_POD10	0.63	0.70	0.77	0.14	–
DIFF_POD12	0.76	0.84	0.92	0.16	–

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 21: **DC Output Levels for Single-ended and Differential POD10 and POD12 Standards(1)(2)**

Symbol	Description	V_{OUT}	Min	Typ	Max	Units
R_{OL}	Pull-down resistance.	V_{OM_DC} (as described in Table 22)	36	40	44	Ω
R_{OH}	Pull-up resistance.	V_{OM_DC} (as described in Table 22)	36	40	44	Ω

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 22: **Table 21 Definitions for DC Output Levels for POD Standards**

Symbol	Description	All Speed Grades	Units
V_{OM_DC}	DC output Mid measurement level (for IV curve linearity).	0.8 x V_{CCO}	V